Kingbright

PHOTOTRANSISTOR

L-53P3C

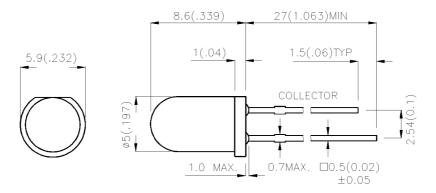
Features

- •MECHANICALLY AND SPECTRALLY MATCHED TO THE L-53 SERIES INFRARED EMITTING LED LAMP.
- •WATER CLEAR LENS.

Description

Made with NPN silicon phototransistor chips.

Package Dimensions



Notes:

- 1. All dimensions are in millimeters (inches).
- 2. Tolerance is ±0.25(0.01") unless otherwise noted.
- 3. Lead spacing is measured where the lead emerge package.
- 4. Specifications are subject to change without notice.

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Electrical / Optical Characteristics at T_A=25°C

Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Condiction
VBR CEO	Collector-to-Emitter Breakdown Voltage	30	-	-	٧	I c=100uA E _e =0mW/cm ²
VBRECO	Emitter-to-Collector Breakdown Voltage	5	-	-	٧	I ∈=100uA E _e =0mW/cm²
VCE (SAT)	Collector-to-Emitter Saturation Voltage	-	-	0.8	٧	I c=2mA E _e =20mW/cm ²
ICEO	Collector Dark Current	-	-	100	nA	Vce=10V E _e =0mW/cm²
TR	Rise Time (10% to 90%)	-	3	-	us	V _{CE} =5V k=1mA R _L =1000Ω
TF	Fall Time (90% to 10%)	-	3	-	us	
I (ON)	On State Collector Current	0.1	0.5	-	mA	V _{CE} =5V Ee=1mW/cm² λ=940nm

Absolute Maximum Ratings at T_A=25°C

Parameter	Maximum Rating			
Collector-to-Emitter Breakdown Voltage	30V			
Emitter-to-Collector Breakdown Voltage	5V			
Power Dissipation at (or below) 25°C Free Air Temperature	100mW			
Operating Temperature Range	-40°C ~ +85°C			
Storage Temperature Range	-40°C ~ +85°C			
Lead soldering Temperature (>5mm for 5sec)	260°C			

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